

International IOR Rectifier

- Logic Level Gate Drive
- Ultra Low On-Resistance
- Surface Mount (IRLR3410)
- Straight Lead (IRLU3410)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	17	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	12	
I_{DM}	Pulsed Drain Current ①⑤	60	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	79	W
	Linear Derating Factor	0.53	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy②⑤	150	mJ
I_{AR}	Avalanche Current①⑤	9.0	A
E_{AR}	Repetitive Avalanche Energy①⑤	7.9	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

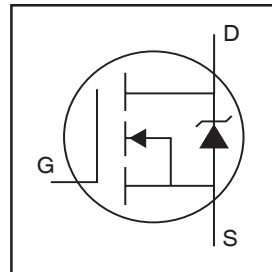
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.9	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

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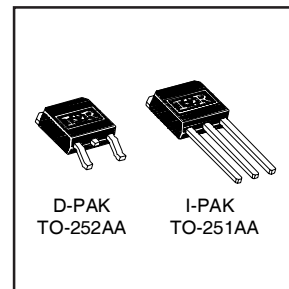
PD - 95087A

IRLR/U3410PbF

HEXFET® Power MOSFET



$V_{DSS} = 100\text{V}$
$R_{DS(on)} = 0.105\Omega$
$I_D = 17\text{A}$



D-PAK
TO-252AA

I-PAK
TO-251AA

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.122	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.105	W	$V_{GS} = 10V, I_D = 10A$ ④
		—	—	0.125		$V_{GS} = 5.0V, I_D = 10A$ ④
		—	—	0.155		$V_{GS} = 4.0V, I_D = 9.0A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	7.7	—	—	S	$V_{DS} = 25V, I_D = 9.0A$ ⑤
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	34	nC	$I_D = 9.0A$
Q_{gs}	Gate-to-Source Charge	—	—	4.8		$V_{DS} = 80V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	20		$V_{GS} = 5.0V$, See Fig. 6 and 13 ④ ⑤
$t_{d(on)}$	Turn-On Delay Time	—	7.2	—	ns	$V_{DD} = 50V$
t_r	Rise Time	—	53	—		$I_D = 9.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	30	—		$R_G = 6.0\Omega, V_{GS} = 5.0V$
t_f	Fall Time	—	26	—		$R_D = 5.5\Omega$, See Fig. 10 ④ ⑤
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑥
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	800	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	160	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	90	—		$f = 1.0\text{MHz}$, See Fig. 5 ⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	17	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ① ⑤	—	—	60		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 9.0A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	140	210	ns	$T_J = 25^\circ\text{C}, I_F = 9.0A$
Q_{rr}	Reverse Recovery Charge	—	740	1100	nC	$di/dt = 100A/\mu s$ ④ ⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 3.1\text{mH}$ $R_G = 25\Omega$, $I_{AS} = 9.0A$. (See Figure 12)
- ③ $I_{SD} \leq 9.0A$, $di/dt \leq 540A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$
- ⑤ Uses IRL530N data and test conditions
- ⑥ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact

** When mounted on 1" square PCB (FR-4 or G-10 Material) .
For recommended footprint and soldering techniques refer to application note #AN-994

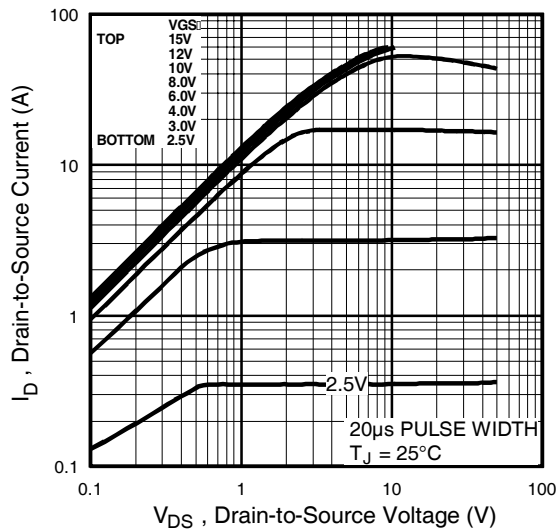


Fig 1. Typical Output Characteristics

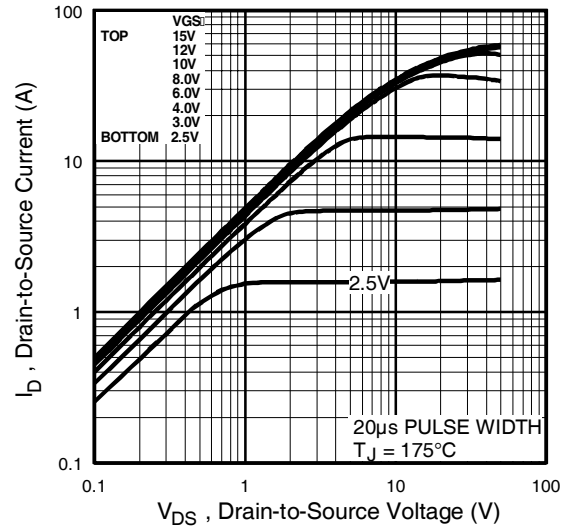


Fig 2. Typical Output Characteristics

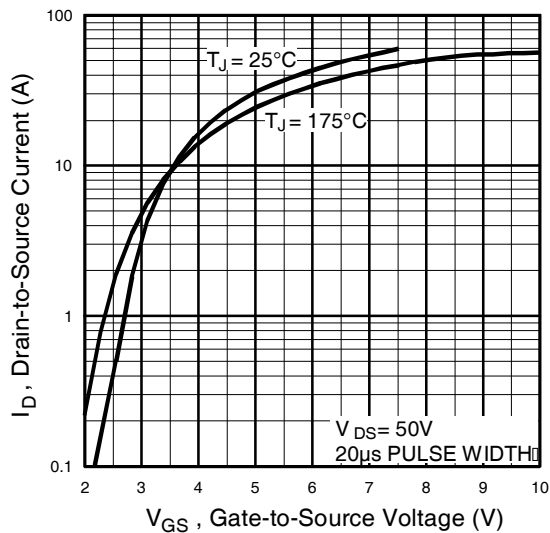


Fig 3. Typical Transfer Characteristics

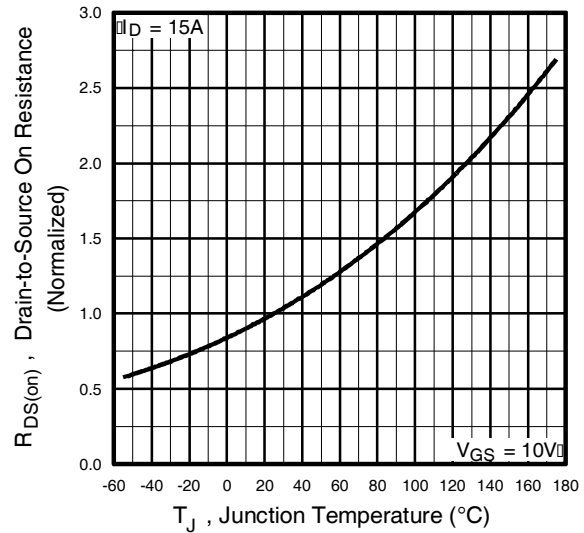


Fig 4. Normalized On-Resistance
Vs. Temperature

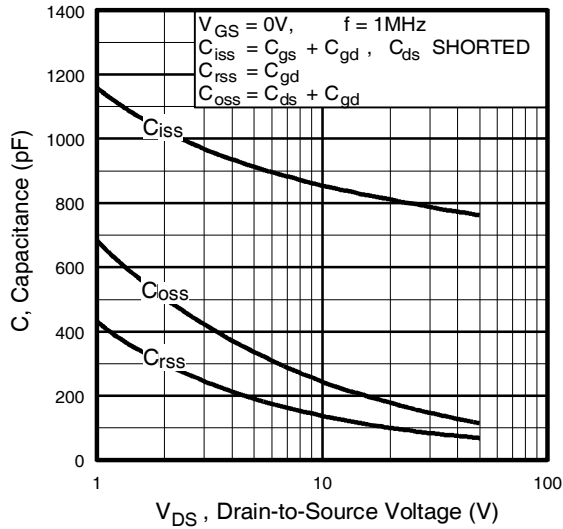


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

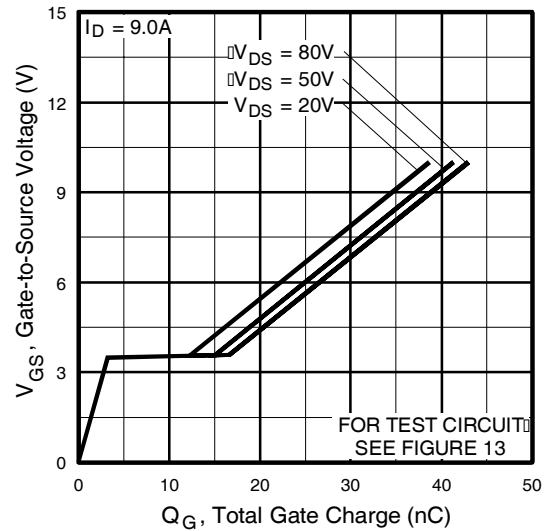


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

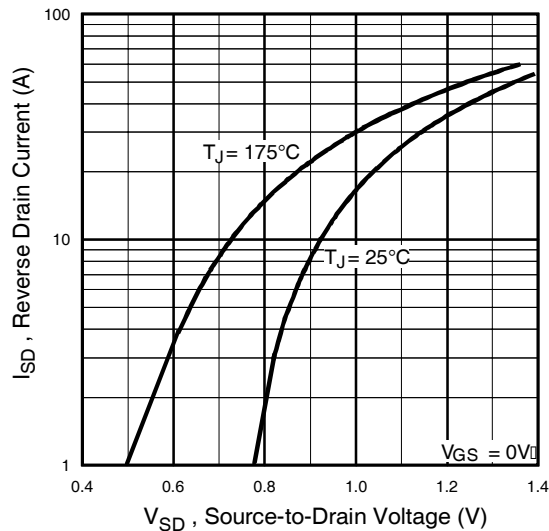


Fig 7. Typical Source-Drain Diode Forward Voltage

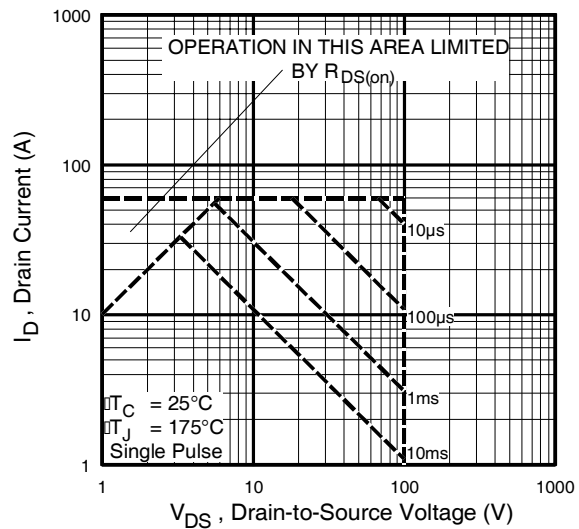


Fig 8. Maximum Safe Operating Area

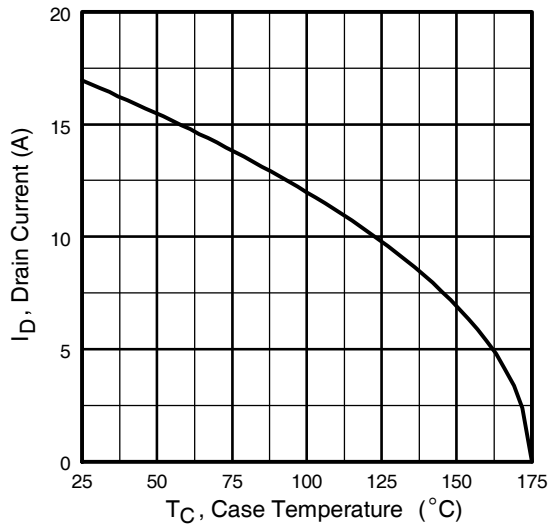


Fig 9. Maximum Drain Current Vs. Case Temperature

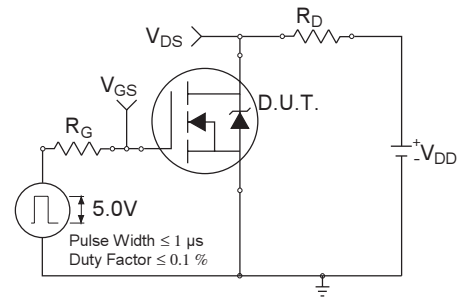


Fig 10a. Switching Time Test Circuit

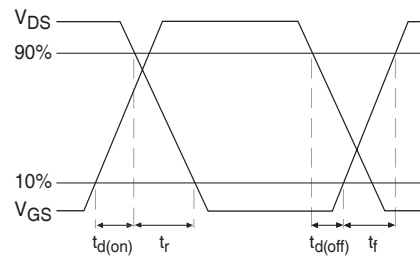


Fig 10b. Switching Time Waveforms

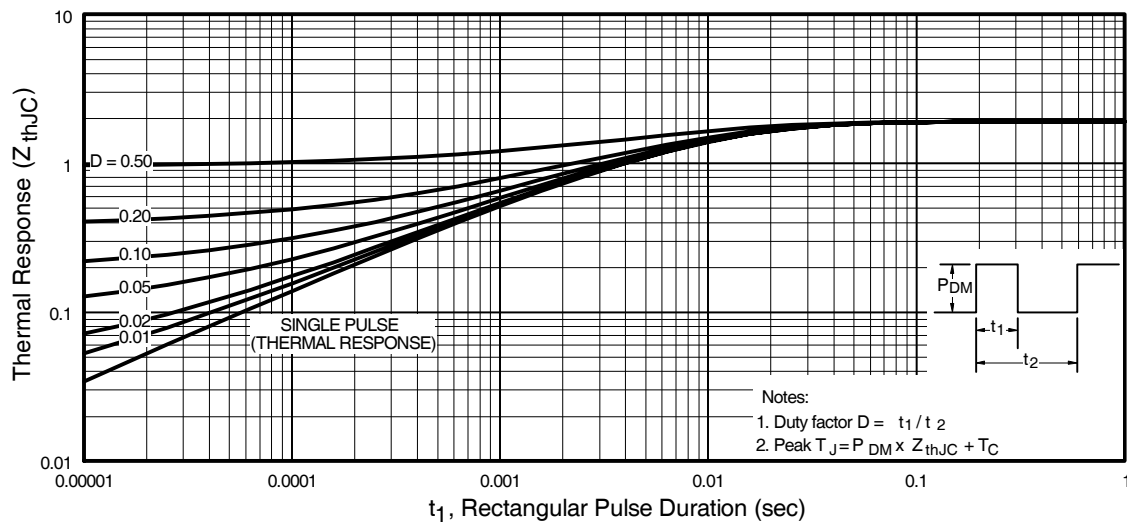


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

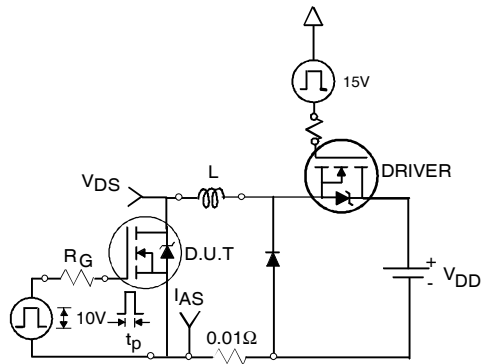


Fig 12a. Unclamped Inductive Test Circuit

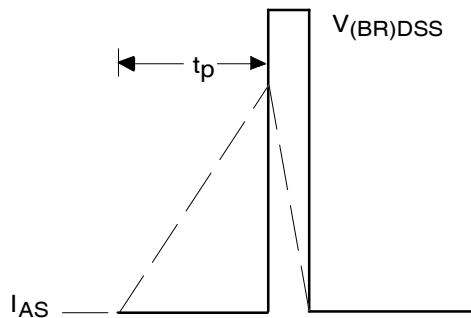


Fig 12b. Unclamped Inductive Waveforms

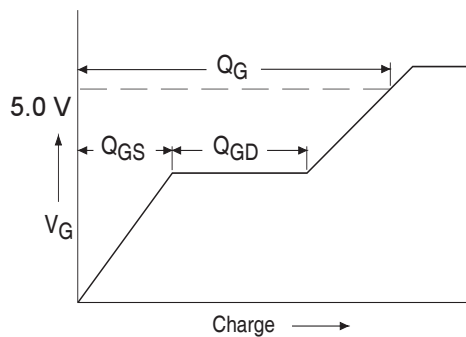


Fig 13a. Basic Gate Charge Waveform

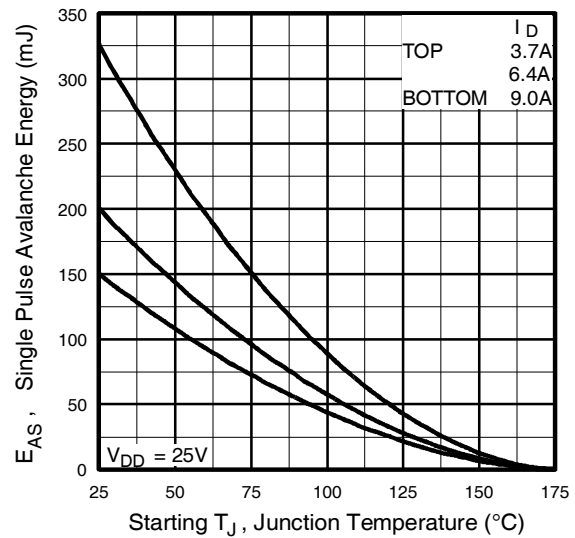


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

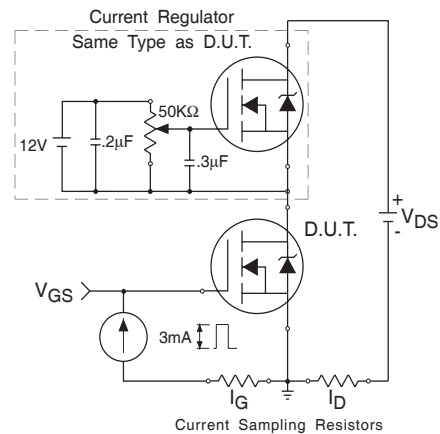


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

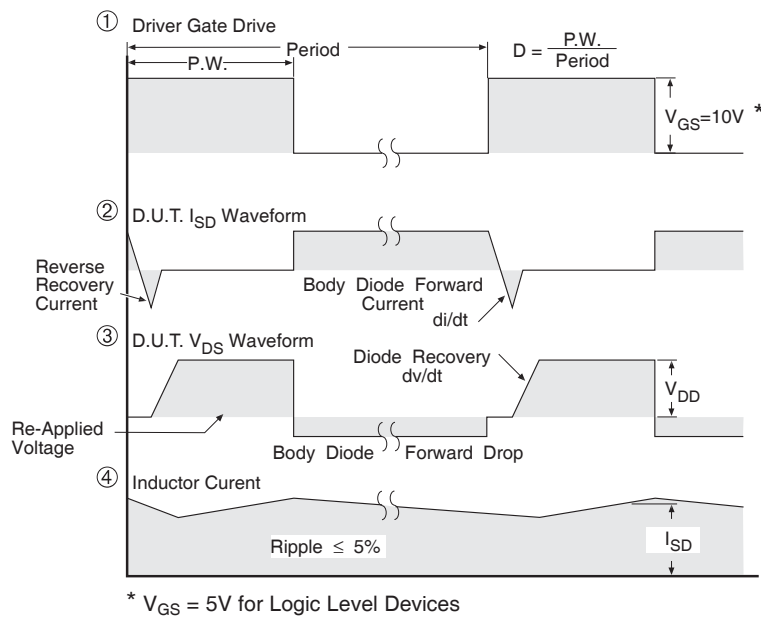
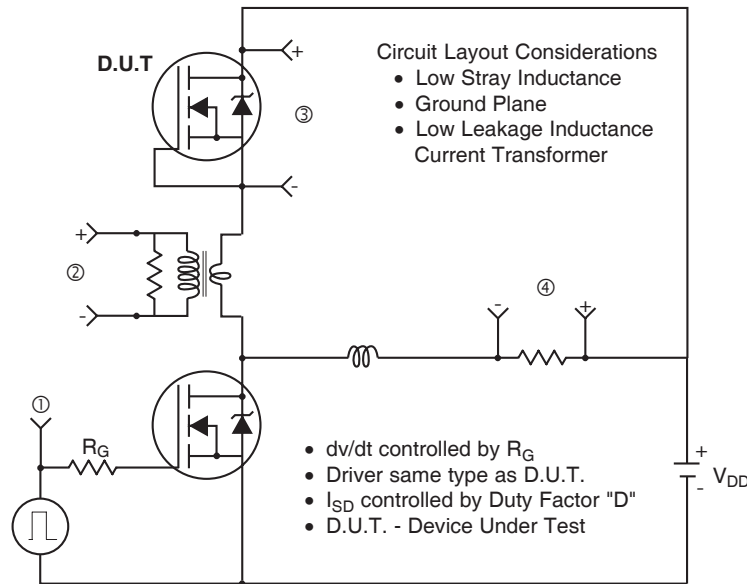
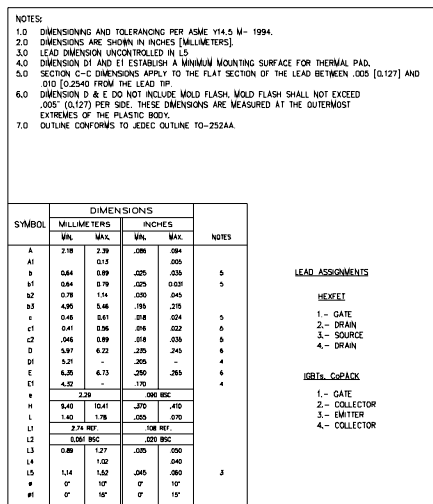


Fig 14. For N-Channel HEXFETS

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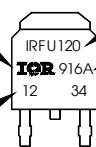
Dimensions are shown in millimeters (inches)



EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 1999
IN THE ASSEMBLY LINE "A"

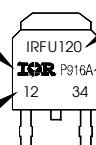
INTERNATIONAL
RECTIFIER
LOGO

ASSEMBLY
LOT CODE



PART NUMBER
✓ DATE CODE
YEAR 9 = 1999
WEEK 16
LINE A

OR



PART NUMBER

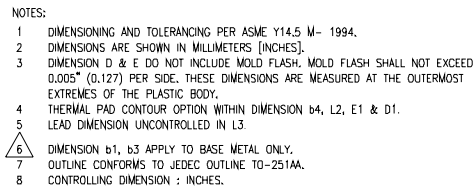
✓ DATE CODE
P = DESIGNATES LEAD-FREE
PRODUCT (OPTIONAL)

YEAR 9 = 1999

WEEK 16

A = ASSEMBLY SITE CODE

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	3, 4
E	6.36	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	Ø	15'	Ø	15'	

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 1999
IN THE ASSEMBLY LINE "A"

Diagram illustrating the marking on the IRFU120 diode package, showing the following fields:

- INTERNATIONAL RECTIFIER LOGO**: Points to the IR logo.
- PART NUMBER**: Points to the text **IRFU120**.
- DATE CODE**: Points to the text **919A**.
- YEAR 9 = 1999**: Points to the text **919A**.
- WEEK 19**: Points to the text **919A**.
- LINE A**: Points to the text **919A**.
- ASSEMBLY LOT CODE**: Points to the text **56 78**.

Diagram illustrating the markings on the IRFU120 MOSFET package:

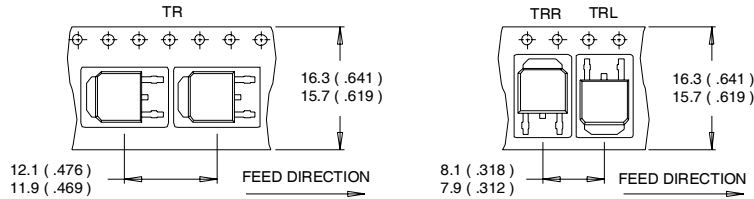
- INTERNATIONAL RECTIFIER LOGO**: Points to the IR logo.
- PART NUMBER**: Points to the text IRFU120.
- DATE CODE**: Points to the text P919A.
- ASSEMBLY LOT CODE**: Points to the text 56 78.

Additional information provided:

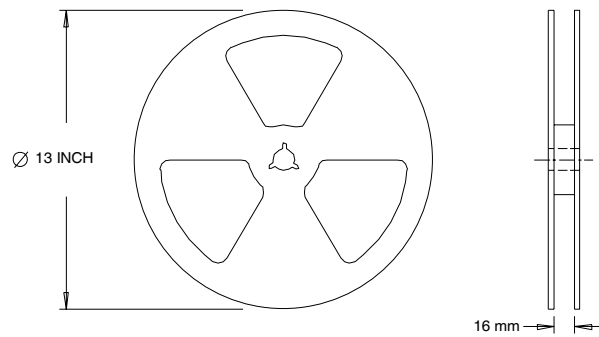
- P = DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)**
- YEAR 9 = 1999**
- WEEK 19**
- A = ASSEMBLY SITE CODE**

D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.

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IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
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Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>

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